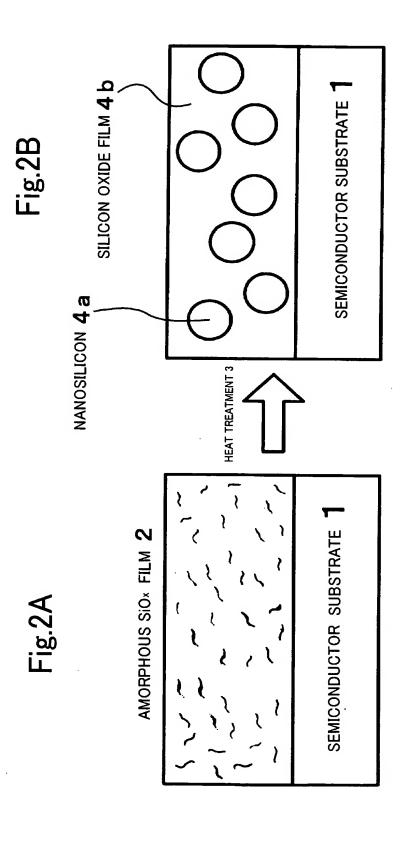
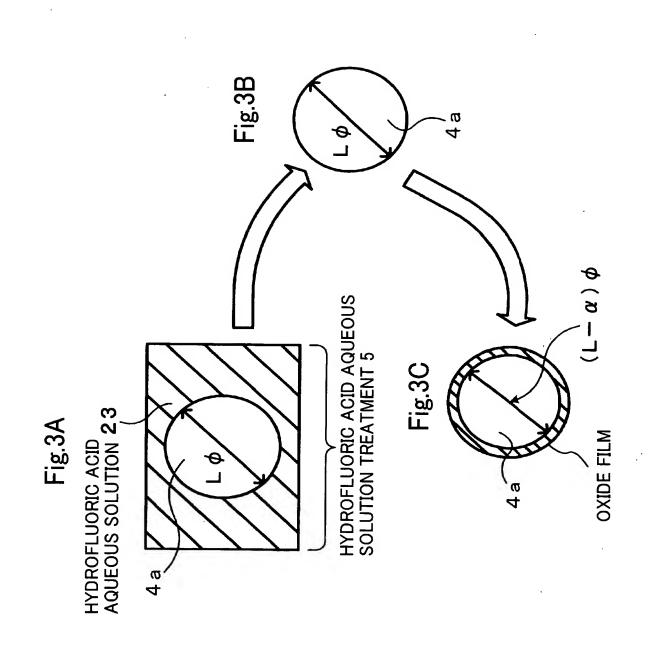
SEMICONDUCTOR SUBSTRATE HYDROFLUORIC ACID AQUEOUS 5 SOLUTION TREATMENT NATURAL OXIDATION TREATMENT 9 THERMAL OXIDATION 6
TREATMENT HYDROFLUORIC ACID AQUEOUS SOLUTION TREATMENT 5 S R 4b SILICON OXIDE FILM 23 HYDROFLUORIC ACID AQUEOUS SOLUTION SEMICONDUCTOR SUBSTRATE Fig.1A 4a NANOSILICON 22 RESIN CONTAINER

Fig.1B





PL STRENGTH (ARBITRARY SCALE)

PL STRENGTH (ARBITRARY SCALE)

400 600 700

WAVELENGTH (nm)

800

